

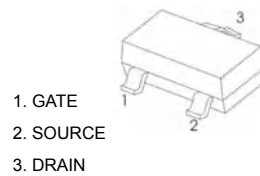
FEATURES

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

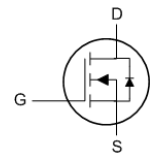
V_{DSS} 60 V
 I_D 3 A
 $R_{DS(ON)}$ 78 m Ω

S10

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current (note 1)	I_{DM}	10	A
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

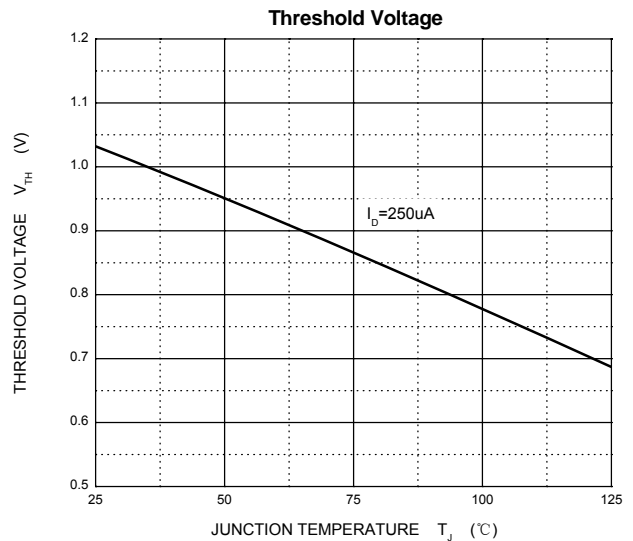
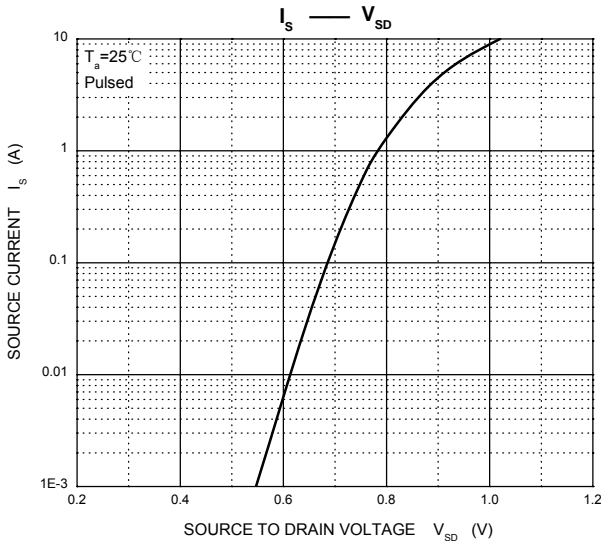
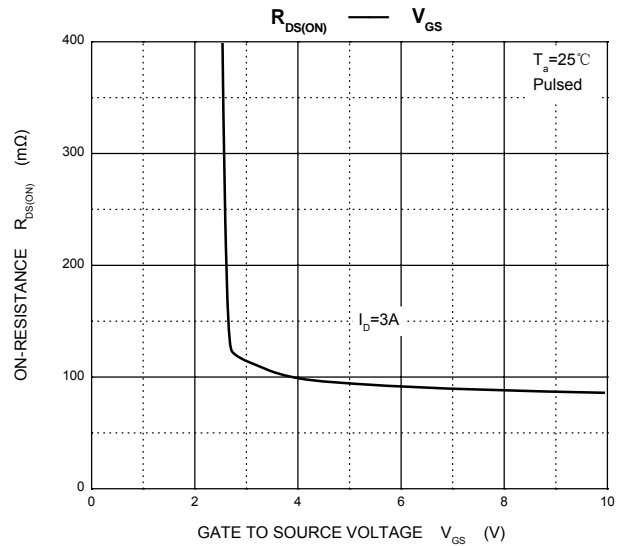
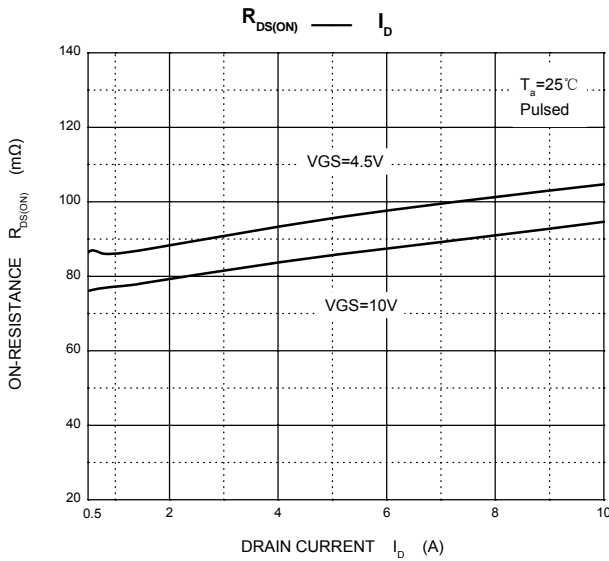
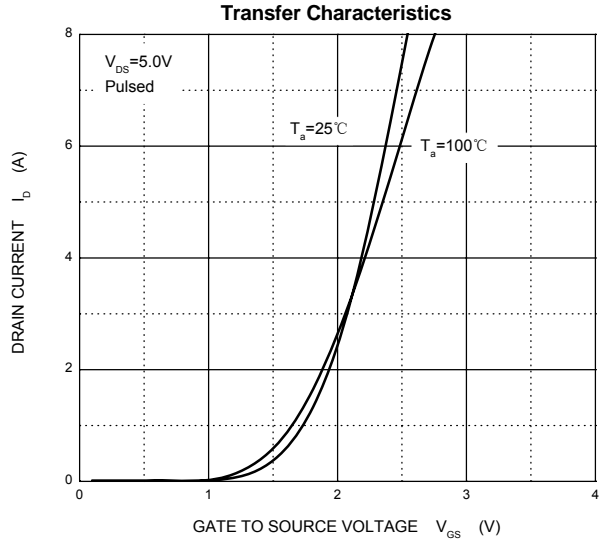
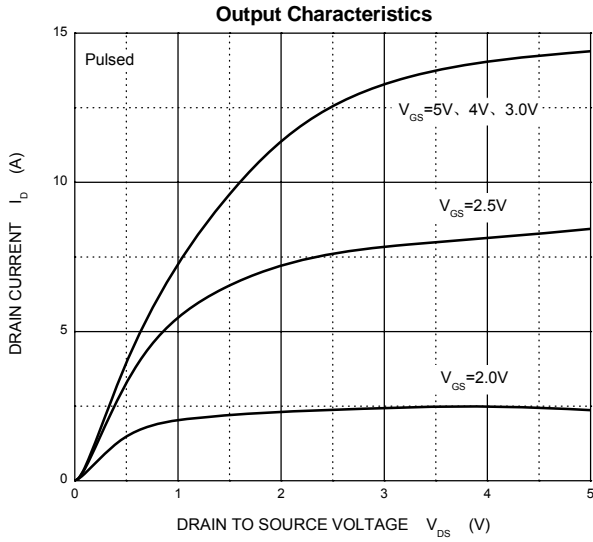
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage (note 3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1		2	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$		78	105	m Ω
		$V_{GS} = 4.5V, I_D = 3A$			125	m Ω
Forward transconductance (note 3)	g_{FS}	$V_{DS} = 15V, I_D = 2A$	1.4			S
Diode forward voltage (note 3)	V_{SD}	$I_S = 3A, V_{GS} = 0V$			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		247		pF
Output Capacitance	C_{oss}			34		pF
Reverse Transfer Capacitance	C_{rss}			19.5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 30V,$ $I_D = 1.5A, R_{GEN} = 1\Omega$		6		ns
Turn-on rise time	t_r			15		ns
Turn-off delay time	$t_{d(off)}$			15		ns
Turn-off fall time	t_f			10		ns
Total Gate Charge	Q_g	$V_{DS} = 30V, V_{GS} = 4.5V, I_D = 3A$		6		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			1.3		nC

Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , $t \leq 10s$.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.
4. Guaranteed by design, not subject to producing.

RATING AND CHARACTERISTIC CURVES



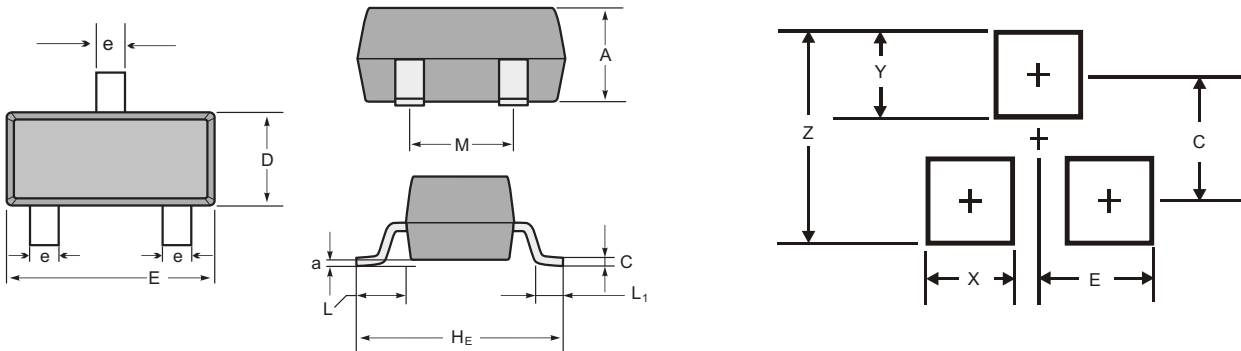
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23



SOT-23 mechanical data

UNIT	A	C	D	E	H_E	e	M	L	L_1	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & reel specification

Tape		Symbol	Dimension (mm)		
		P0	4.00±0.10		
		P1	4.00±0.10		
		P2	2.00±0.10		
		D0	1.55±0.10		
		D1	1.05±0.10		
		E	1.55±0.10		
		F	3.60±0.10		
		W	8.00±0.10		
		A0	3.80±0.20		
		B0	3.25±0.20		
		K0	1.45±0.10		
		T	0.25±0.05		
		7" Reel		D2	178.0±3.0
				D3	55Min.
D4	R24.0±3.0				
G	R82.0±3.0				
I	13.0±2.0				
W1	11.0±3.0				
Quantity: 3000PCS					